10EC63

# Sixth Semester B.E. Degree Examination, Aug./Sept. 2020 Microelectronics Circuits 

Time: 3 hrs .
Max. Marks:100
Note: Answer any THREE full questions from Part-A and any TWO full questions from Part-B.

## PART - A

1 a. Derive an expression for drain current of a MOSFET in different regions of operation.
(05 Marks)
b. Explain how the MOSFET can be used as an amplifier and as a switch.
(05 Marks)
c. Explain different biasing methods in MOS amplifier circuits.
(10 Marks)
2 a. Draw the development of the T-equivalent circuit model for the MOSFET. (05 Marks)
b. The NMOS and PMOS transistors in the circuit shown in Fig. Q2 (b) are matched with $\mathrm{K}_{\mathrm{n}}^{\prime}\left(\frac{\omega_{\mathrm{n}}}{\mathrm{L}_{\mathrm{n}}}\right)=\mathrm{K}_{\dot{p}}^{\prime}\left(\frac{\omega_{\mathrm{P}}}{\mathrm{L}_{\mathrm{P}}}\right)=1 \frac{\mathrm{~mA}}{\mathrm{~V}^{2}}$ and $\mathrm{V}_{\mathrm{tn}}=-\mathrm{V}_{\mathrm{tp}}=1 \mathrm{~V}$. Assuming $\lambda=0$ for both devices, find the drain currents $\mathrm{i}_{\mathrm{DN}}$ and $\mathrm{i}_{\mathrm{DP}}$ and the voltage $\mathrm{V}_{0}$ for $\mathrm{V}_{1}=0 \mathrm{~V},+2.5 \mathrm{~V}$ and -2.5 V . (05 Marks)

c. For a common gate amplifier with $g_{m}=1 \mathrm{~mA} / V$ and $R_{D}=15 \mathrm{~K} \Omega$. Find $R_{i n}, R_{\text {out }}, A V_{O}, A_{V}$ and $G_{V}$ for $R_{L}=15 \mathrm{~K} \Omega$ and $R_{\text {sig }}=50 \Omega$. What will the overall voltage can become for $\mathrm{R}_{\text {sig }}=1 \mathrm{~K} \Omega, 10 \mathrm{~K} \Omega$ and $100 \mathrm{~K} \Omega$.
(10 Marks)
3 a. What is MOSFET scaling? Explain about short channel effect due to scaling. (05 Marks)
b. Explain with neat diagram of Wilson MOS mirror.
(05 Marks)
c. Given $\mathrm{V}_{\mathrm{DD}}=3 \mathrm{~V}$ and $\mathrm{I}_{\mathrm{REF}}=100 \mu \mathrm{~A}$ it is required to design a basic MOSFET constant current source to obtain an output current whole nominal value is $100 \mu \mathrm{~A}$. Find R if $\mathrm{Q}_{1}$ and $\mathrm{Q}_{2}$ are matched and have channel length's of $1 \mu \mathrm{~m}$, channel width's of $10 \mu \mathrm{~m}, \mathrm{~V}_{\mathrm{t}}=0.7 \mathrm{~V}$ and $\mathrm{K}_{\mathrm{n}}^{\prime}=200 \mu \mathrm{~A} / \mathrm{V}^{2}$. What is the lowest possible value of $\mathrm{V}_{0}$ ? Assuming that for this process technology the early voltage $\mathrm{V}_{\mathrm{A}}^{\prime}=20 \mathrm{~V} / \mu \mathrm{m}$, find the output resistance of the current source. Also, find the change in output current resulting from $\mathrm{a}+1-\mathrm{V}$ change in $\mathrm{V}_{0}$.
(05 Marks)
d. Draw the BJT constant current source circuit and explain it.
(05 Marks)
4 a. In common gate amplifier with active load, obtain $3-\mathrm{dB}$ frequency for using open circuit time constants. Draw the circuit required for determining $\mathrm{R}_{\mathrm{gs}}$ and $\mathrm{R}_{\mathrm{gd}}$.
( $\mathbf{1 0}$ Marks)
b. Consider a source follower circuit, specified as follows : W/L $=7.2 \mu \mathrm{~m} / 0.36 \mu \mathrm{~m}$, $\mathrm{I}_{\mathrm{D}}=100 \mu \mathrm{~A}, \mathrm{~g}_{\mathrm{m}}=1.25 \mathrm{~mA} / \mathrm{V}, \chi=0.2, \mathrm{r}_{0}=20 \mathrm{~K} \Omega, \mathrm{R}_{\text {sig }}=20 \mathrm{~K} \Omega, \mathrm{R}_{\mathrm{L}}=10 \mathrm{~K} \Omega$, $\mathrm{C}_{\mathrm{gs}}=20 \mathrm{fF}, \mathrm{C}_{\mathrm{gd}}=5 \mathrm{fF}, \mathrm{C}_{\mathrm{L}}=15 \mathrm{fF}$. Find three capacitances $\mathrm{C}_{\mathrm{gd}}, \mathrm{C}_{\mathrm{gs}}$ and $\mathrm{C}_{\mathrm{L}}$. Find $\tau_{\mathrm{H}}$ and the percentage contribution to it from each of three capacitances. Find $\mathrm{f}_{\mathrm{H}}$.
(10 Marks)

5 a. Draw the two stage Op-Amp CMOS OpAmp configuration and briefly explain obtain overall open loop gain.
(08 Marks)
b. The differential amplifier in figure uses transistors with $\beta=100$. Evaluate the following:
(i) The input differential resistance $\mathrm{R}_{\mathrm{id}}$.
(ii) The overall differential voltage gain $V_{0} / \bigvee_{\text {sig }}$ (Neglect the effect of $r_{0}$ ).
(iii) The worst case common mode gain if the two collector resistances are accurate to within $\pm 1 \%$.
(iv) The CMRR in dB .
(v) The input common mode resistance (assuming that the early voltage $\mathrm{V}_{\mathrm{A}}=100 \mathrm{~V}$ )
(12 Marks)


Fig. Q5 (b)

## PART - B

6 a. Explain briefly with expressions the properties of Negative feedback.
(10 Marks)
b. Explain about Shunt-Shunt feedback amplifier with diagram and obtain the expression for input impedance and output impedance.
(10 Marks)
7 a. Explain instrumentation amplifier with neat circuit diagram.
(05 Marks)
b. Use the superposition principle to find the output voltage of the circuit shown in Fig. Q7 (b).


(05 Marks)

Fig. Q7 (b)
c. Explain logarithmic and antilogarithmic amplifiers with neat diagrams.
(10 Marks)
8 a. Explain the dynamic operation of a CMOS inverter.
(10 Marks)
b. Sketch a CMOS logic circuit that realizes the function $\mathrm{Y}=\overline{\mathrm{ABC}+\mathrm{DE}}$, using AOI gate.
(04 Marks)
c. Explain charge sharing problem in dynamic 3-input NAND circuits.
(06 Marks)

